

IN THE CLAIMS:

Please note that all claims currently pending and under consideration in the referenced application are shown below, in clean form, for clarity. Claims 16 and 23 have been amended herein. Please enter these claims as amended. Also attached as Appendix C is a marked up version of the claims amended herein pursuant to 37 C.F.R. § 1.121(c)(1)(ii).

Please amend the claims as follows:

16. (Amended) A method of packaging at least one semiconductor die in a high density arrangement comprising:
providing a substrate;
providing a flexible interposer including a first surface having a plurality of electrical contacts for electrically connecting at least one semiconductor die to a substrate, a second surface, and a plurality of vias extending completely through said flexible interposer from said first surface to said second surface;
providing at least one semiconductor die having a plurality of bond pads on a first surface thereof;
attaching said at least one semiconductor die to said flexible interposer forming an intermediate structure, said interposer being folded around said at least one semiconductor die, said at least one die being in electrical communication with said substrate through said flexible interposer; and
attaching said intermediate structure to said substrate.

17. The method of claim 16, wherein said vias are filled with conductive metal.

18. The method of claim 16, wherein said second surface surrounds at least three sides of the at least one semiconductor die around which said interposer is folded.

19. (Previously Amended) The method of claim 16, wherein said second surface of said interposer surrounds at least two sides of the at least one semiconductor die around which said interposer is folded.

20. The method of claim 16, wherein said bond pads are in electrical communication with said electrical contacts through said vias in the flexible interposer.

21. The method of claim 16, wherein said interposer folds around more than two semiconductor die in a serpentine fashion around groups including at most two semiconductor die therein.

22. The method of claim 16, further comprising applying electrical contacts to a top surface of a high density semiconductor package to attach semiconductor devices to said package.

23. (Amended) A method of forming a high density semiconductor package comprising:
providing at least one semiconductor die having a plurality of bond pads on a surface of said at least one die;
providing an interposer including a first surface having a plurality of electrical contacts, a second surface, and a plurality of vias extending completely through said interposer from said first surface to said second surface;
attaching said at least one die to said interposer to form an intermediate packaging structure;
providing a substrate;
attaching said substrate to said intermediate structure; and
connecting between said substrate and said at least one semiconductor die.

24. (Previously Amended) The method of claim 23, wherein said attaching said at least one die further comprises:
attaching multiple semiconductor die in groups of two semiconductor die, said semiconductor die having a back-to-back configuration, a back side of one semiconductor die substantially contacting a back side of another semiconductor die of a group.

25. The method of claim 23, wherein said electrical contacts and said bond pads provide electrical communication through said vias of the flexible interposer.

26. The method of claim 23, further comprising:
forming electrical contacts on a top surface of said package to attach semiconductor device components.
